RJK60S5DPQ-E0

600V - 20A - SJ MOS FET
High Speed Power Switching

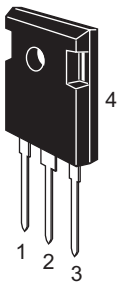
R07DS0734EJ0200
Rev.2.00
Jan 23, 2013

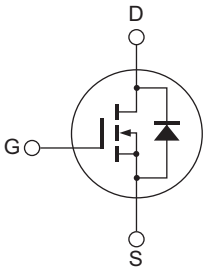
Features

- Superjunction MOSFET
- Low on-resistance
  $R_{DS(on)}$ = 0.150 Ω typ. (at I_D = 10 A, V_{GS} = 10 V, Ta = 25°C)
- High speed switching
  t_f = 23 ns typ. (at I_D = 10 A, V_{GS} = 10 V, R_L = 30 Ω, Rg = 10 Ω, Ta = 25°C)

Outline

RENESAS Package code: PRSS0003ZE-A
(Package name: TO-247)





1. Gate
2. Drain
3. Source
4. Drain

Absolute Maximum Ratings

(Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage		V_{DSS}	600	V
Gate to source voltage		V_{GSS}	+30, –20	V
Drain current	Tc = 25°C	I_D Note1	20	A
	Tc = 100°C	I_D Note1	12.6	A
Drain peak current		$I_{D\ (pulse)}$ Note1	40	A
Body-drain diode reverse drain current		I_{DR} Note1	20	A
Body-drain diode reverse drain peak current		$I_{DR\ (pulse)}$ Note1	40	A
Avalanche current		I_{AP} Note2	5	A
Avalanche energy		E_{AR} Note2	1.36	mJ
MOSFET dv/dt ruggedness		dv/dt Note3	150	V/ns
Channel dissipation		Pch Note4	192.3	W
Channel to case thermal impedance		θch-c	0.65	°C/W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	–55 to +150	°C

Notes: 1. Limited by Tch max.
2. STch = 25°C, Tch ≤ 150°C
3. Value at Tj = 25°C, V_{DS} ≤ 480 V
4. Value at Tc = 25°C

Electrical Characteristics

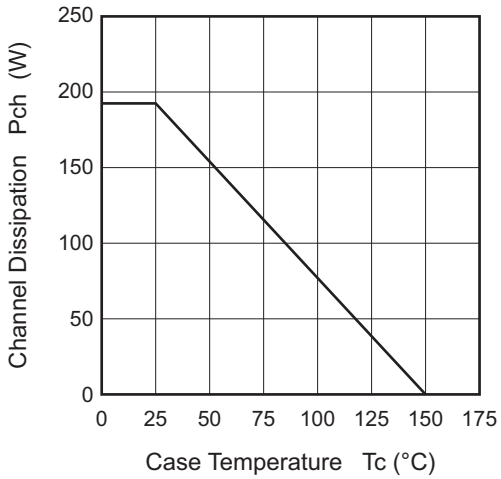
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	—	—	V	I_D = 10 mA, V_{GS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	1	mA	V_{DS} = 600 V, V_{GS} = 0
Gate to source leak current	I_{GSS}	—	—	±0.1	μA	V_{GS} = +30V, –20 V, V_{DS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	3	—	5	V	V_{DS} = 10 V, I_D = 1 mA
Static drain to source on state resistance	$R_{DS(on)}$	—	0.150	0.178	Ω	I_D = 10 A, V_{GS} = 10 V Note5
	$R_{DS(on}$	—	0.375	—	Ω	Ta = 150°C I_D = 10 A, V_{GS} = 10 V Note5
Gate resistance	Rg	—	2.5	—	Ω	f = 1 MHz V_{DS} = 25 V, V_{GS} = 0
Input capacitance	Ciss	—	1600	—	pF	V_{DS} = 25 V V_{GS} = 0 f = 100kHz
Output capacitance	Coss	—	2160	—	pF	
Reverse transfer capacitance	Crss	—	8.2	—	pF	
Turn-on delay time	$t_{d(on)}$	—	23	—	ns	I_D = 10 A V_{GS} = 10 V R_L = 30 Ω Rg = 10 Ω Note5
Rise time	t_r	—	25	—	ns	
Turn-off delay time	$t_{d(off)}$	—	49	—	ns	
Fall time	t_f	—	23	—	ns	
Total gate charge	Qg	—	27	—	nC	V_{DD} = 480 V V_{GS} = 10 V I_D = 20 A Note4
Gate to source charge	Qgs	—	10.5	—	nC	
Gate to drain charge	Qgd	—	8.5	—	nC	
Body-drain diode forward voltage	V_{DF}	—	0.96	1.60	V	I_F = 20 A, V_{GS} = 0 Note5
Body-drain diode reverse recovery time	t_{rr}	—	400	—	ns	I_F = 20 A V_{GS} = 0 di_F/dt = 100 A/μs Note5
Body-drain diode reverse recovery current	I_{rr}	—	25	—	A	
Body-drain diode reverse recovery charge	Q_{rr}	—	5.6	—	μC	

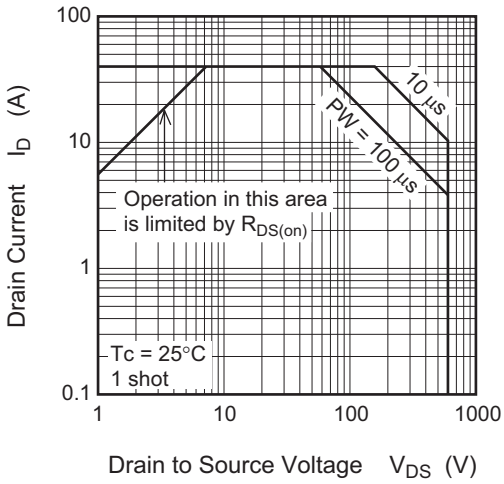
Notes: 5. Pulse test

Main Characteristics

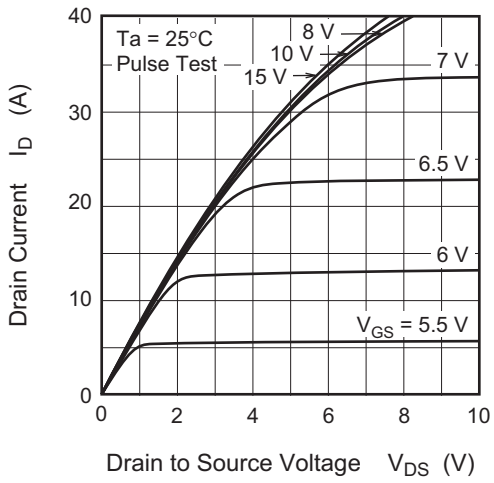
Channel Dissipation vs. Case Temperature



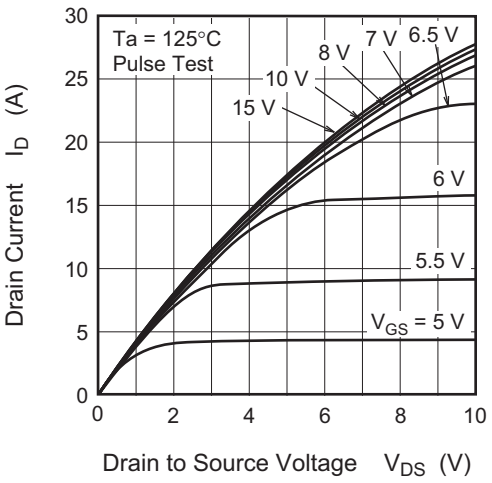
Maximum Safe Operation Area



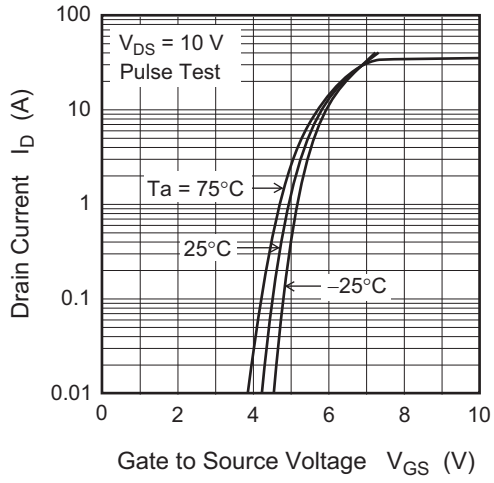
Typical Output Characteristics



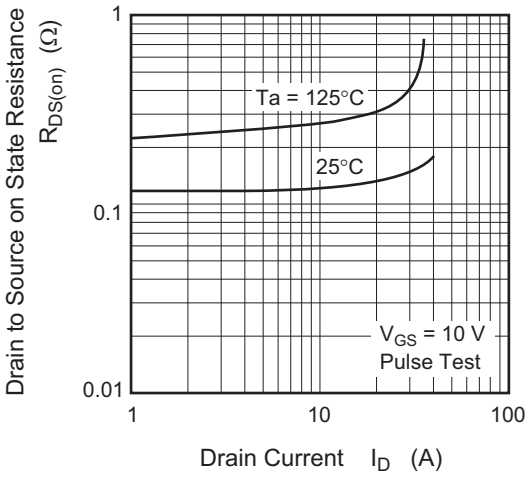
Typical Output Characteristics



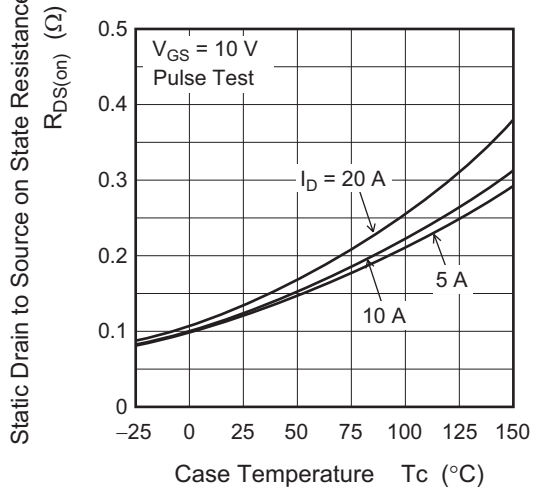
Typical Transfer Characteristics



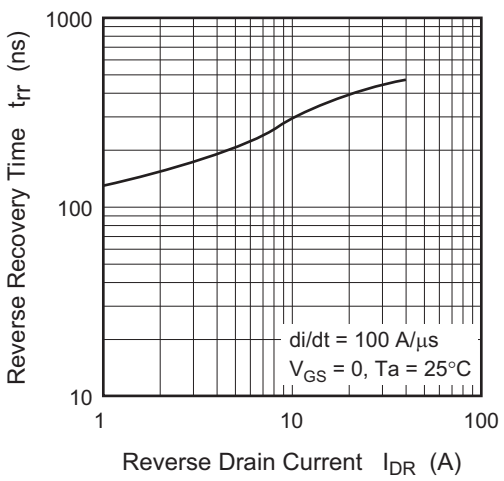
Static Drain to Source on State Resistance vs. Drain Current (Typical)



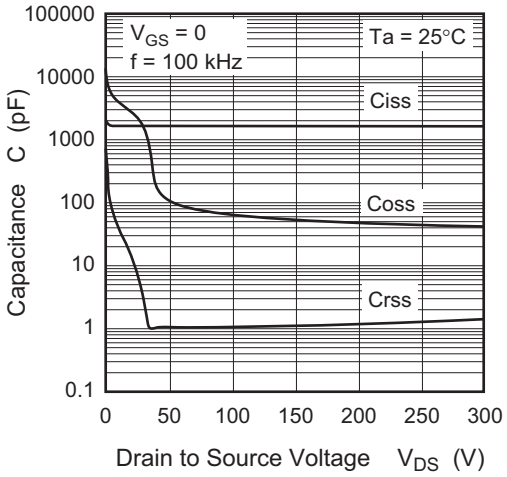
Static Drain to Source on State Resistance vs. Temperature (Typical)



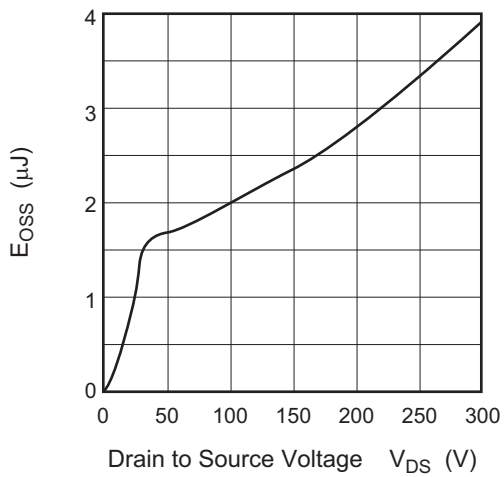
Body-Drain Diode Reverse Recovery Time (Typical)



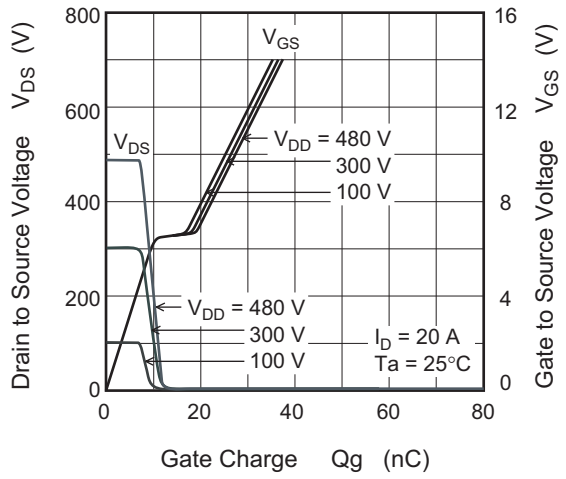
Typical Capacitance vs. Drain to Source Voltage



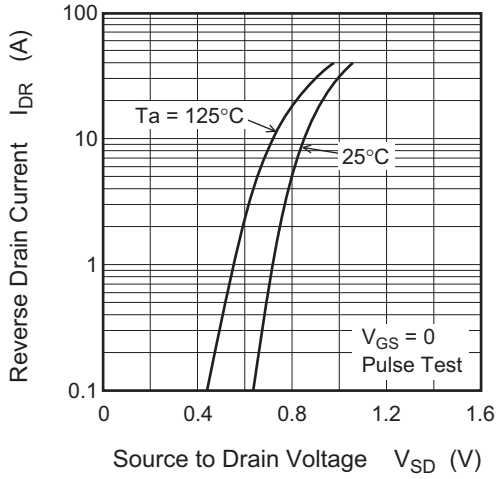
C_{OSS} Stored Energy (Typical)



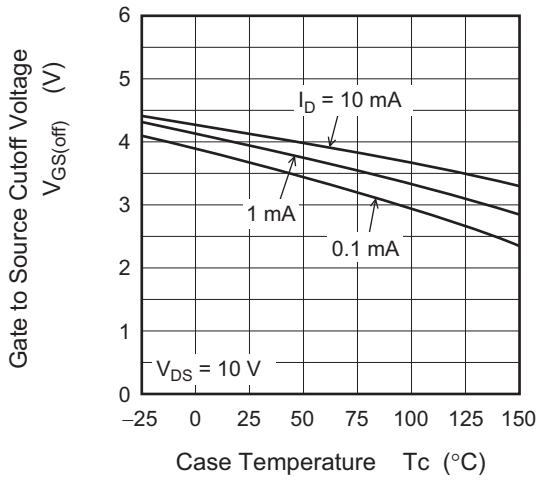
Dynamic Input Characteristics (Typical)



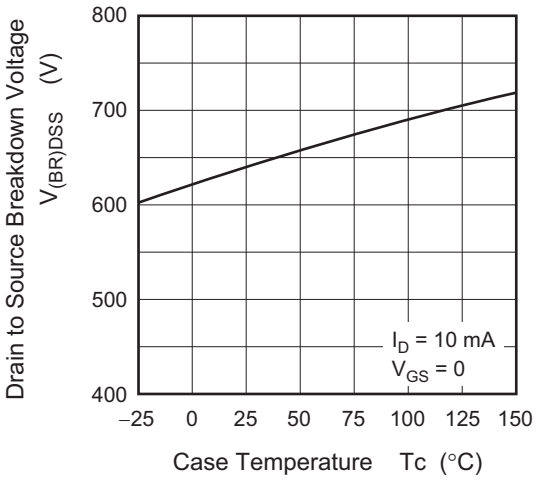
Reverse Drain Current vs. Source to Drain Voltage (Typical)



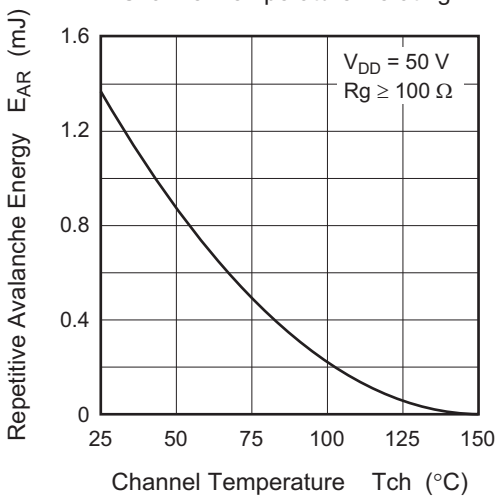
Gate to Source Cutoff Voltage vs. Case Temperature (Typical)



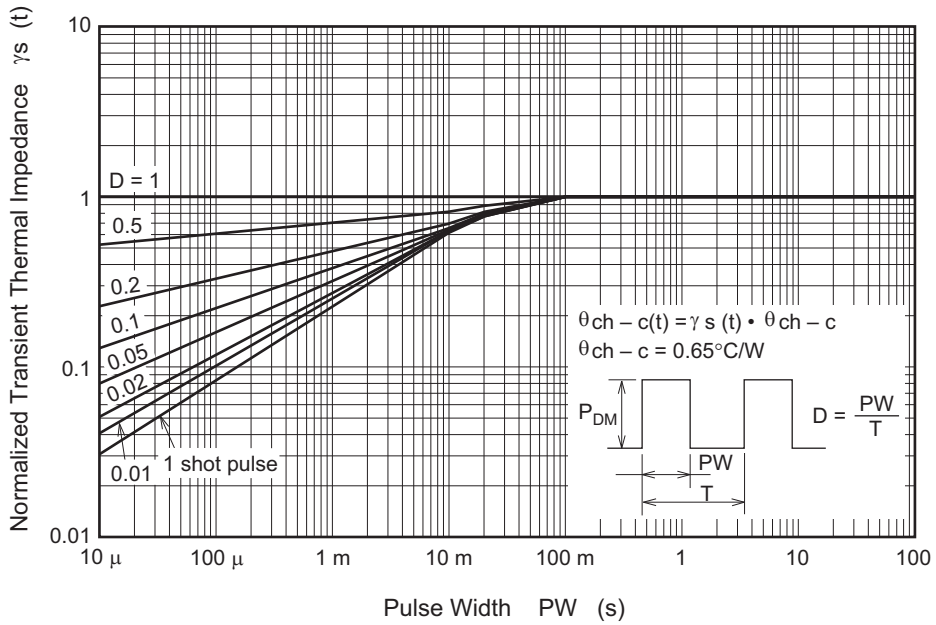
Drain to Source Breakdown Voltage vs. Case Temperature (Typical)



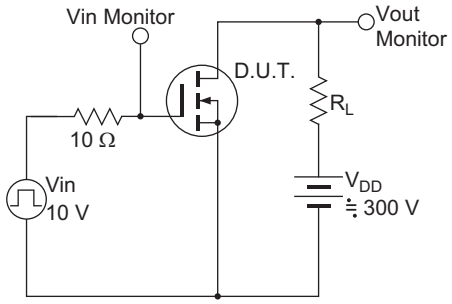
Maximum Avalanche Energy vs. Channel Temperature Derating



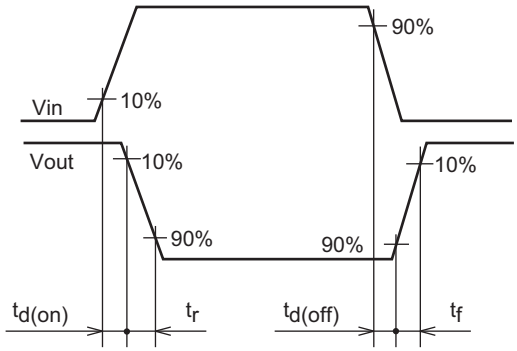
Normalized Transient Thermal Impedance vs. Pulse Width



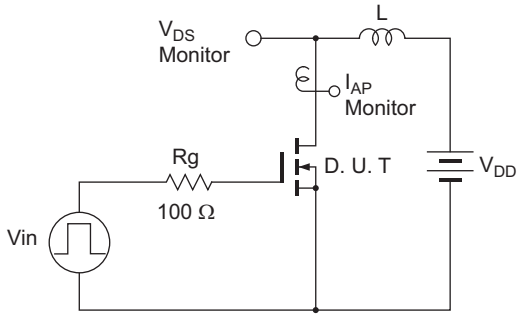
Switching Time Test Circuit



Waveform

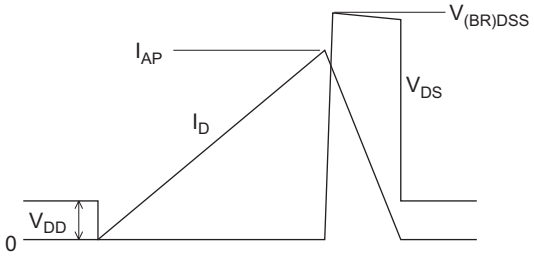


Avalanche Test Circuit



Avalanche Waveform

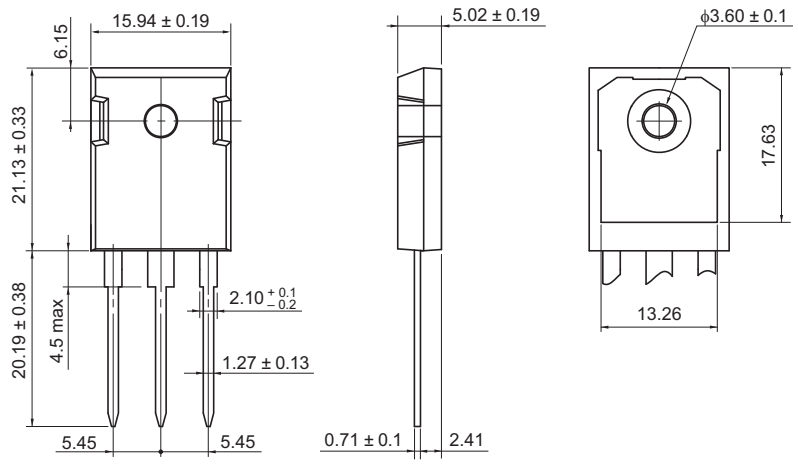
$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



Package Dimension

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
TO-247	—	PRSS0003ZE-A	—	6.0g

Unit: mm



Ordering Information

Orderable Part Number	Quantity	Shipping Container
RJK60S5DPQ-E0#T2	30 pcs	Tube

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Renesas Electronics America Inc.
2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd.
11F., Samik Lavied' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141

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